

# **TMR Sensor Datasheet**

### 1. General Introduction

The T1302 linear sensor utilizes a unique push-pull Wheatstone bridge composed of four unshielded TMR sensor elements. The unique bridge design provides a high sensitivity differential output that is linearly proportional to a magnetic field applied parallel to the surface of the sensor package, and it provides superior temperature compensation of the output. The T1302 is available in 6mm x 5mm x 1.5mm SOP8 and 3mm  $\times$  3mm  $\times$  0.75mm DFN8L package.

#### 2. Features

Tunneling Magneto resistance (TMR) Technology High Sensitivity Large Dynamic Range Low Power Consumption Excellent Thermal Stability

### 3. Applications

Magnetic Field Sensing Current Sensors Displacement Sensing Rotary Position Sensors

### 4. Specifications

## Specification (V<sub>CC</sub>=1.0V, T<sub>A</sub>=25°C, Differential Output)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Supply Voltage	Vcc	Operating		1	7	V
Supply Current	Icc	Output Open		33 <sup>(2)</sup>		μA
Resistance(SOP8)	R			30 <sup>(2)</sup>		KOhm
Sensitivity	SEN	Fit @±800e		3.1		mV/V/Oe
Saturation Field	H <sub>sat</sub>			±150		Oe
Non-Linearity	NONL	Fit @±80Oe		1.5		%FS
Offset Voltage	V <sub>offset</sub>		-8		8	mV/V
Hysteresis	Hys	Fit @±800e		0.5		Oe
Temperature Coefficient of Resistance	TCR	H = 0 Oe		-600		PPM/°C
Temperature Coefficient of Sensitive	TCS			-300		PPM/°C

#### Notes

### 5. Absolute Maximum Ratings

#### **Absolute Maximum Ratings**

Parameter	Symbol	Limit	Unit
Supply Voltage	Vcc	7	V
Reverse Supply Voltage	V <sub>RCC</sub>	7	V
Max Exposed Field	HE	4000	Oe <sup>(1)</sup>
ESD Voltage	V <sub>ESD</sub>	4000	V
Operating Temperature	T <sub>A</sub>	-40~125	°C
Storage Temperature	T <sub>stg</sub>	-50 ~150	°C

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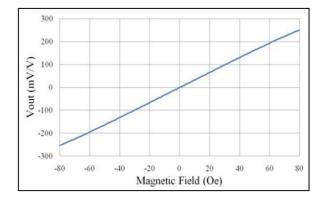
<sup>(1) 1</sup> Oe (Oersted) = 1 Gauss in air = 0.1 millitesla = 79.8 A/m.

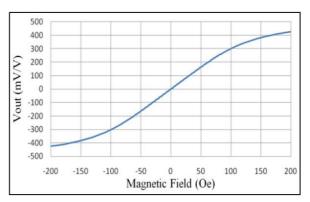
<sup>(2)</sup> Custom resistance may be available upon request.



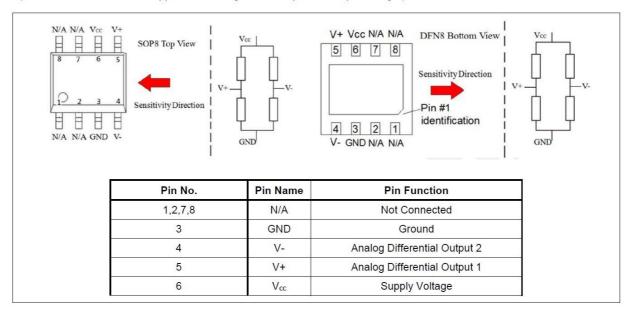
### 6 · Transfer Curve

The following figure shows the response of the T1302 to an applied magnetic field in the range of ±80 Oe (left) and ±200 Oe (right) when the T1302 is biased at 1 V.





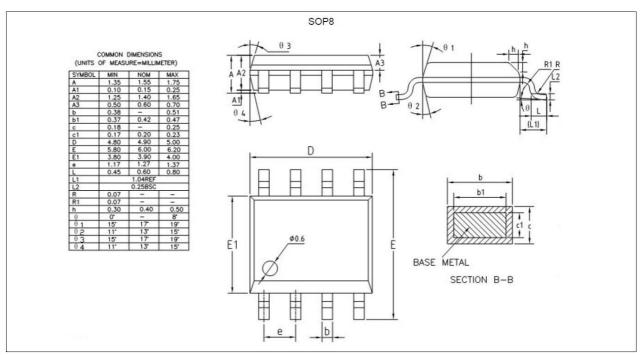
#### (Arrow indicates direction of applied field that generates a positive output voltage.)

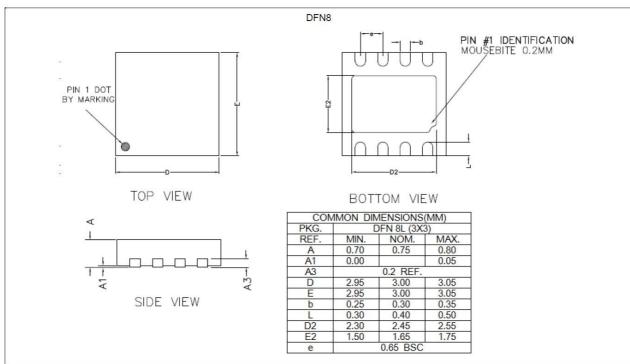


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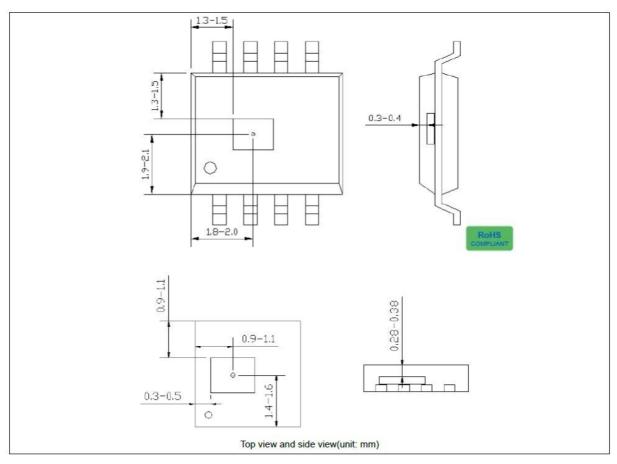
# 7. Packing Instructions







### **TMR Sensor Position**



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